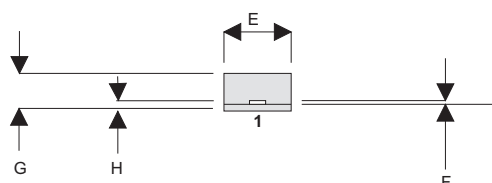
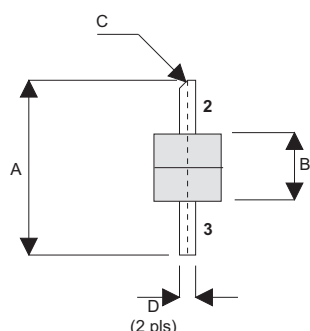


MECHANICAL DATA



DP

PIN 1 SOURCE

PIN 2 DRAIN

PIN 3 GATE

DIM	mm	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	1.52	0.13	0.060	0.005
E	6.35	0.13	0.250	0.005
F	0.13	0.03	0.005	0.001
G	3.56	0.51	0.140	0.020
H	0.64	0.13	0.024	0.005

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 10W – 28V – 1GHz SINGLE ENDED

FEATURES

• SIMPLIFIED AMPLIFIER DESIGN

• SUITABLE FOR BROAD BAND

APPLICATIONS

• LOW C_{rss}

• SIMPLE BIAS CIRCUITS

• LOW NOISE

• HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

• VHF/UHF COMMUNICATIONS
from 50 MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	42W
BV_{DSS}	Drain – Source Breakdown Voltage	65V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	4A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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Issue 1

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS} Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 10mA	65			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 28V V _{GS} = 0			0.8	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 0.8A	0.72			S
G _{PS} Common Source Power Gain	P _O = 10W	10			dB
η Drain Efficiency	V _{DS} = 28V I _{DQ} = 0.4A	40			%
VSWR Load Mismatch Tolerance	f = 1GHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 0 V _{GS} = -5V f = 1MHz			48	pF
C _{oss} Output Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			24	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			2	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 4.2°C / W
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